



DMN2020LSN

N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 2KV
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

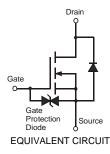
- Case: SC-59
- Case Material Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 2
- Ordering Information: See Page 2
- Weight: 0.014 grams (approximate)

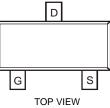
SC-59





TOP VIEW





Pin Out Configuration

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage Continuous			V _{GSS}	±12	V
Continuous Drain Current	Steady State	T _A = 25°C T _A = 85°C	Ι _D	6.9 4.5	A
Pulsed Drain Current (Note 4)			I _{DM}	30	А

Thermal Characteristics

Characteristic	Symbol	Value	Units
Power Dissipation (Note 3)	PD	0.61	W
Thermal Resistance, Junction to Ambient $@T_A = 25^{\circ}C$ (Note 3)	$R_{ heta JA}$	204	°C /W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes: 1. No purposefully added lead.

2. Diodes Inc.'s "Green" Policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

3. Device mounted on FR-4 PCB, with minimum recommended pad layout.

4. Repetitive rating, pulse width limited by junction temperature.

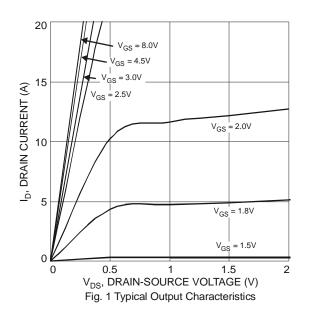


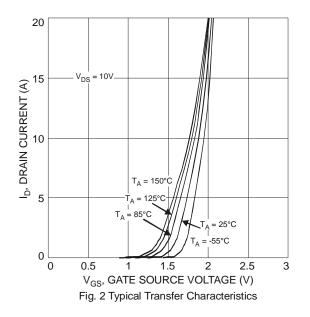
Electrical Characteristics @T_A = 25°C unless otherwise specified

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Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	-	-	V	$V_{GS} = 0V, I_{D} = 250\mu A$
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	-	-	1.0	μA	$V_{DS} = 20V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	-	-	±10	μA	$V_{GS} = \pm 12V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 5)						
Gate Threshold Voltage	V _{GS(th)}	0.5	1.0	1.5	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
Static Drain-Source On-Resistance	P		13	20 28	mΩ	$V_{GS} = 4.5V, I_D = 9.4A$
	R _{DS (ON)}	-	18		111.5.2	$V_{GS} = 2.5V, I_{D} = 8.3A$
Forward Transfer Admittance	Y _{fs}	-	16	-	S	$V_{DS} = 5V, I_{D} = 9.4A$
Diode Forward Voltage	V _{SD}	-	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 1.3A$
DYNAMIC CHARACTERISTICS (Note 6)						
Input Capacitance	C _{iss}	-	1149	-	pF	
Output Capacitance	Coss	-	157	-	pF	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	-	142	-	pF	
Gate Resistance	Rg	-	1.51	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge	Qq	-	11.6	-	nC	
Gate-Source Charge	Q _{qs}	-	2.7	-	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$ $I_{D} = 9.4A$
Gate-Drain Charge	Q_{gd}	-	3.4	-	nC	$I_D = 9.4A$
Turn-On Delay Time	t _{D(on)}	-	11.67	-	ns	
Turn-On Rise Time	t _r	-	12.49	-	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$
Turn-Off Delay Time	t _{D(off)}	-	35.89	-	ns	$R_{GEN} = 6\Omega, I_D = 1A$
Turn-Off Fall Time	t _f	-	12.33	-	ns]

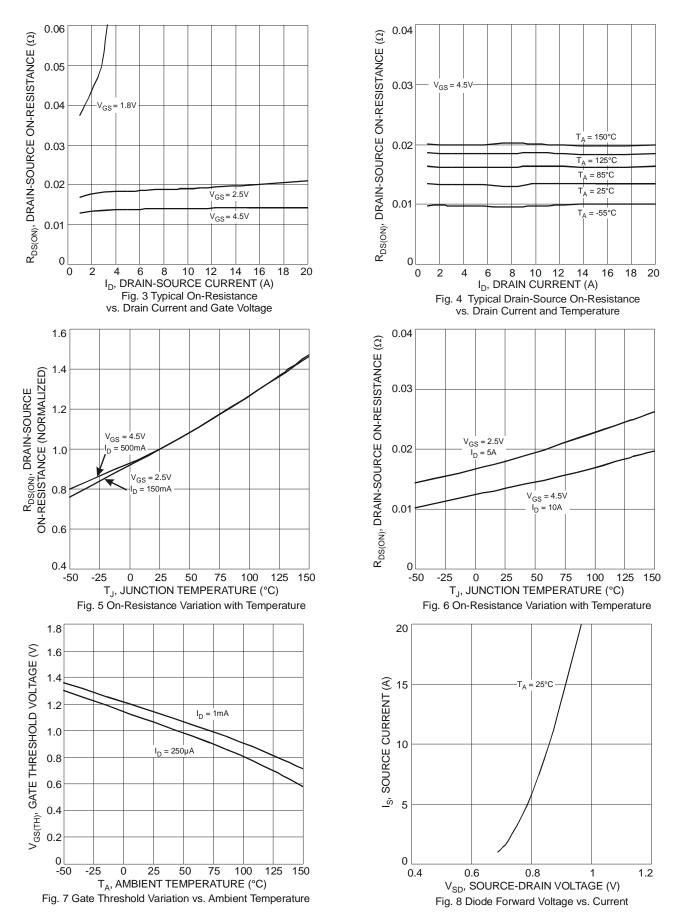
Notes:

Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to production testing.



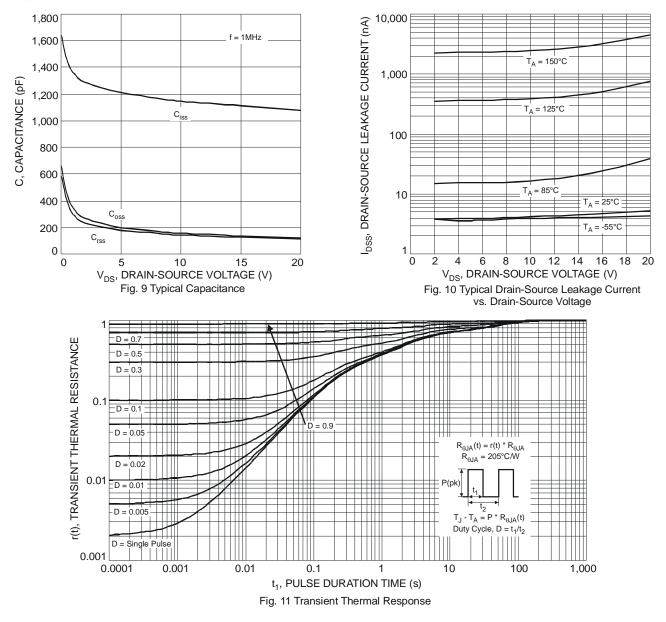








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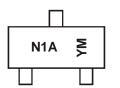


Ordering Information (Note 7)

Part Number	Case	Packaging
DMN2020LSN-7	SC-59	3000/Tape & Reel

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



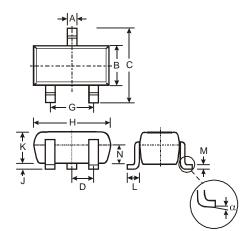
N1A = Product Type Marking Code YM = Date Code Marking Y = Year (ex: W = 2009) M = Month (ex: 9 = September)

Date Code	Key
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Year	2009)	2010		2011	20	12	2013		2014	2	2015
Code	W		Х		Y	Ž	7	А		В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

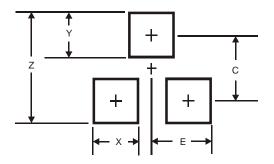


Package Outline Dimensions



SC-59						
Dim	Min	Max	Тур			
Α	0.35	0.50	0.38			
В	1.50	1.70	1.60			
С	2.70	3.00	2.80			
D	-	-	0.95			
G	-	-	1.90			
Н	2.90	2.90 3.10				
J	0.013	0.10	0.05			
κ	1.00	1.30	1.10			
L	0.35	0.55	0.40			
М	0.10	0.20	0.15			
Ν	0.70	0.80	0.75			
α	0°	8°	-			
All	All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)
Z	3.4
Х	0.8
Y	1.0
С	2.4
E	1.35



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